

UTC UNISONIC TECHNOLOGIES CO., LTD

01N30

Preliminary

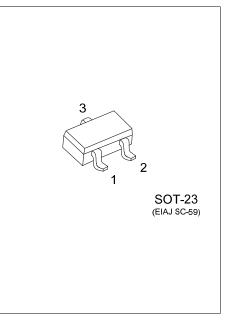
0.1A, 300V N-CHANNEL **POWER MOSFET**

DESCRIPTION

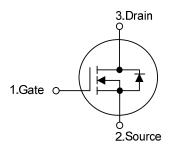
The UTC 01N30 is a N-channel mode power MOSFET using UTC's advanced technology to provide customers with a minimum on-state resistance, low gate charge and superior switching performance.

FEATURES

- * $R_{DS(ON)} \le 9.0\Omega$ @ V_{GS}=10V, I_D=0.05A
- * High switching speed
- * 100% avalanche tested



SYMBOL



ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Packing	
Lead Free	Halogen Free	Package	1	2	3	Facking	
01N30L-AE3-R	01N30G-AE3-R	SOT-23	G	S	D	Tape Reel	
Note: Pin Assignment: G: Gate S: Source D: Drain							
01N30G-AE3-R	(1)Packing Type (2)Package Type (3)Green Package	 (1) R: Tape Reel (2) AE3: SOT-23 (3) G: Halogen Free and Lead Free, L: Lead Free 					



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATINGS	UNIT	
Drain-Source Voltage	V _{DSS}	300	V	
Gate-Source Voltage	V _{GSS}	±30	V	
Continuous Drain Current	ID	0.1	А	
Avalanche Current	I _{AR}	0.1	А	
Power Dissipation	PD	0.3	W	
Junction Temperature	TJ	+150	°C	
Storage Temperature	T _{STG}	-55 ~ +150	°C	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

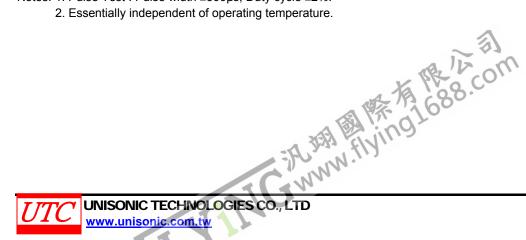
2. Repetitive Rating: Pulse width limited by maximum junction temperature.

ELECTRICAL CHARACTERISTICS

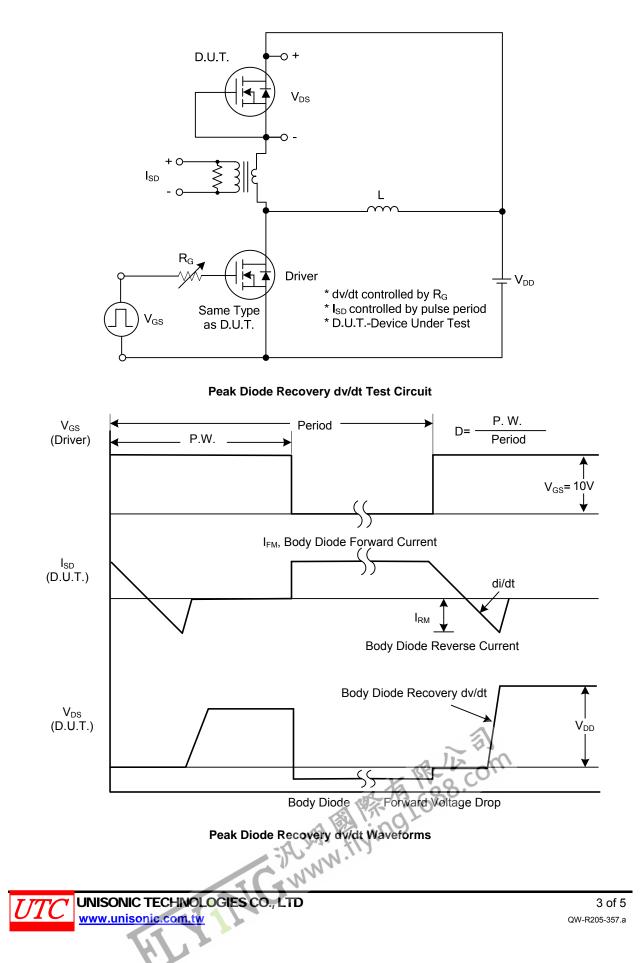
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250μA, V _{DS} =0V	300			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =300V			10	μA
Gate-Source Leakage Current		V _{GS} =+30V, V _{DS} =0V			±100	nA
Reverse	I _{GSS}	V_{GS} =-30V, V_{DS} =0V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	I _D =250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =0.05A			9.0	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}			94.2		рF
Output Capacitance	C _{OSS}	V _{GS} =0V, V _{DS} =25V, f=1MHz		14.1		рF
Reverse Transfer Capacitance	C _{RSS}			12.1		рF
SWITCHING PARAMETERS						
Total Gate Charge	Q_{G}			4.8		nC
Gate to Source Charge	Q _{GS}	−V _{DS} =30V, V _{GS} =10V, I _D =1.3A −I _G = 100µA (Note1, 2)		0.3		nC
Gate to Drain Charge	Q_{GD}	I_{G} = 100µA (Note 1, 2)		0.5		nC
Turn-ON Delay Time	t _{D(ON)}			16		ns
Rise Time	t _R	V _{DS} =50V, V _{GS} =10V, I _D =0.5A,		16.8		ns
Turn-OFF Delay Time	t _{D(OFF)}	R _G =25Ω (Note1, 2)		63.2		ns
Fall-Time	t _F			38.8		ns
SOURCE- DRAIN DIODE RATINGS AND	CHARACTERI	ISTICS				
Maximum Body-Diode Continuous Current	Is				0.1	А
Maximum Body-Diode Pulsed Current	I _{SM}				0.4	А
Drain-Source Diode Forward Voltage	V _{SD}	I _S =0.1A			1.4	V
Reverse Recovery Time	t _{rr}	V _{GS} =0V, I _S =0.1A,		57.2		ns
Reverse Recovery Charge	Q _{rr}	dI _F /dt=100A/µs		54.8		nC

Notes: 1. Pulse Test : Pulse width ≤300µs, Duty cycle ≤2%.

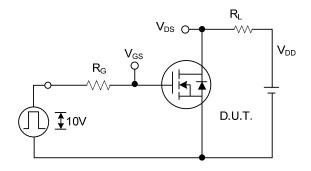
2. Essentially independent of operating temperature.



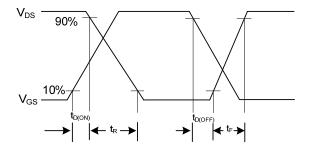
TEST CIRCUITS AND WAVEFORMS



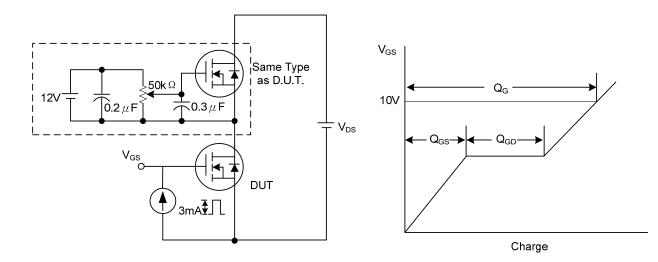
TEST CIRCUITS AND WAVEFORMS





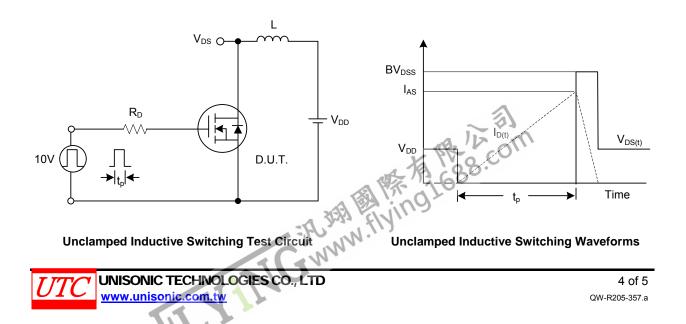


Switching Waveforms



Gate Charge Test Circuit

Gate Charge Waveform



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